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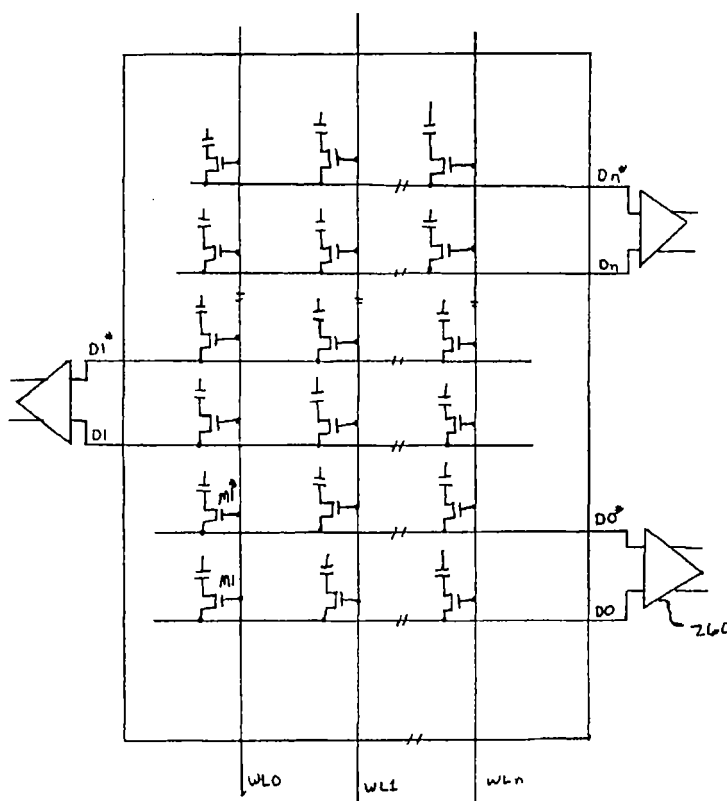
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(54) Title: DEVICE AND METHOD FOR USING COMPLEMENTARY BITS IN A MEMORY ARRAY

(57) Abstract: An apparatus and method of operating an open digit line and a folded digit line DRAM memory array having a plurality of memory cells wherein, in a plan view, each memory cell, in one embodiment, has an area of $6f^2$. One method comprises, storing a first bit in a first memory cell and storing a second bit that is complementary to the first bit in a second memory cell. The first bit and the second bit form a data bit. The data bit is read by comparing a voltage difference between the first memory cell and the second memory cell.

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ACTION

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